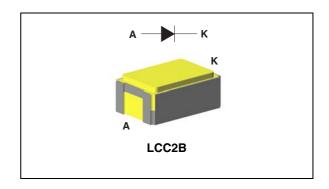


1N5811U

Aerospace 6 A fast recovery rectifier

Features

- Aerospace applications
- Surface mount hermetic package
- High thermal conductivity materials
- Very small conduction losses
- Negligible switching losses
- Extremely fast switching
- Low forward voltage drop
- Package weight: 0.18 g
- Target radiation qualification
 - 150 krad (Si) low dose rate
 - 3 Mrad (Si) high dose rate
- Under ESCC qualification



Description

This power ultrafast recovery rectifier is designed and packaged to comply with the ESCC5000 specification for aerospace products. It is housed in a surface mount hermetically sealed LCC2B package whose footprint is 100% compatible with industry standard solutions in D5B.

The 1N5811U is suitable for switching mode power supplies and high frequency DC to DC converters such as low voltage high frequency inverter, free wheeling or polarity protection.

Table 1. Device summary⁽¹⁾

Order code	ESCC detailed specification	Quality level	Lead finish	EPPL	I _{F(AV)}	V _{RRM}	T _{j(max)}	V _{F (max)}
1N5811UB1	-	Engineering model	Gold plated	-				
1N5811U01B	5101/013/11	Flight part	Gold plated	Υ	6 A	150 V	175 °C	0.995 V
1N5811U02B	5101/013/12	Flight part	Solder dip	Υ				

^{1.} Contact ST sales office for information about the specific conditions for products in die form and QML-Q versions.

July 2009 Doc ID 16005 Rev 1 1/7

www.Data Characteristics 1N5811U

1 Characteristics

Table 2. Absolute ratings (limiting values)

Symbol	Parameter	Value	Unit	
V_{RRM}	Repetitive peak reverse voltage	150	V	
I _{F(RMS)}	Forward rms current		10	Α
I _{F(AV)}	Average forward rectified current $T_c = 135$ °C, $\delta = 0.5$		6	Α
ı	Forward surge current	t _p = 8.3 ms sinusoidal	105	Α
I _{FSM}	$t_p = 10 \text{ ms sinusoidal}$		100	A
T _{stg}	Storage temperature range	-65 to + 175	°C	
T _j	Maximum operating junction temperature	175	°C	
T _{sol}	Maximum soldering temperature (1)	245	°C	

^{1.} Maximum duration 5 s. The same package must not be resoldered until 3 minutes have elapsed.

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
R _{th (j-c)}	Junction to case	6.5	°C/W

Table 4. Static electrical characteristics

Symbol	Parameter	Tests conditions		Min.	Тур.	Max.	Unit
	Reverse current	T _j = 25 °C	V _R = 150 V	-	-	2	
I _R ⁽¹⁾		T _j = 125 °C	V _R = 150 V	-	-	30	μΑ
'R`		T _j = 25 °C	V - 160 V	-	-	10	μΑ
		T _j = -65 °C	V _R = 160 V	-	-	10	
	Forward voltage	T _j = 25 °C	I _F = 3 A	-	-	865	
		T _j = 25 °C		-	-	900	
V _F ⁽²⁾		T _j = 125 °C	I _F = 4 A	-	-	800	mV
		T _j = -65 °C		-	-	1075	
		T _j = 25 °C	I _F = 6 A	-	-	955	

^{1.} Pulse test : tp = 5 ms, δ < 2%

To evaluate the conduction losses use the following equation:

$$P = 0.68 \times I_{F(AV)} + 0.03 I_{F}^{2}(RMS)$$

^{2.} Pulse test : tp = 680 μ s, δ < 2%

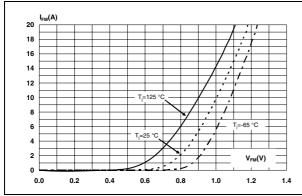
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Table 5. Dynamic characteristics

Symbol	Parameter Test conditions		Min.	Тур	Max.	Unit
t _{RR} Reverse recovery time		$I_F = I_R = 1 \text{ A}, I_{RR} = 0.1 \text{ A}, dI/dt = -100 \text{ A/}\mu\text{s}, (min)$			30	ns
t _{RR}	Theverse recovery time	$I_F = 1 \text{ A, } V_r = 30 \text{ V, } dI/dt = -50 \text{ A/}\mu\text{s,}$			35	115
V _{FP}	Forward recovery voltage	I _{FM} = 500 mA			2.2	V
t _{FR}	Forward recovery time	$I_{FM} = 500 \text{ mA}, V_{FR} = 1.1 \text{ x V}_{F}$			15	ns
C _j	Diode capacitance	V _R = 10 V, F = 1 MHz			60	pF

Figure 1. Forward voltage drop versus forward current (typical values)

Figure 2. Forward voltage drop versus forward current (maximum values)



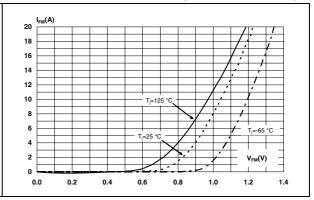
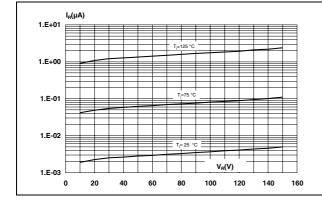
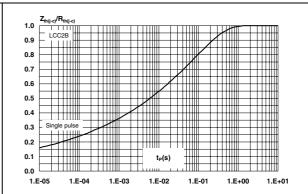


Figure 3. Reverse leakage current versus reverse voltage applied (typical values)

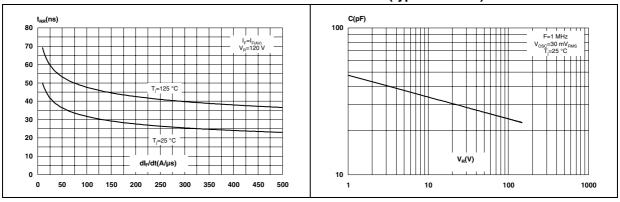
Figure 4. Relative variation of thermal impedance, junction to case, versus pulse duration





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Figure 5. Reverse recovery time versus dI_F/dt Figure 6. Junction capacitance versus reverse voltage applied (typical values)



4/7 Doc ID 16005 Rev 1

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Package information

2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Dimensions Ref. **Millimeters** Inches Min. Min. Max. Тур. Max. Typ. $A^{(1)}$ 2.04 2.23 2.42 0.080 0.088 0.095 0.207 0.213 0.220 В 5.27 5.4 5.6 С 0.137 0.143 0.150 3.49 3.62 3.82 0.082 D 1.71 1.90 2.09 0.067 0.075 0.71 0.019 0.028 0.028 Ε 0.48 F 0.055 1.4 G 3.32 0.131 Н 0.072 1.82 0.15 0.006 0.15 0.006 r1 0.20 800.0 r2 Note 1: The anode is identified by metallization in two top internal angles and the index mark.

Table 6. Leadless chip carrier 2 (LCC2B) package dimensions

^{1.} Measurement prior to solder coating the mounting pads on bottom of package

3 Ordering information

Table 7. Ordering information⁽¹⁾

Order code	ESCC detailed specification	Package	Lead finish	Marking	EPPL	Weight	Packing
1N5811UB1	-		Gold plated	11UB1	-	0.18 g	
1N5811U01B	5101/013/11	LCC2B	Gold plated	11U01B	Υ	0.18 g	Waffle pack
1N5811U02B	5101/013/12		Solder dip	11U02B	Υ	0.16 g	F ->=

Contact ST sales office for information about the specific conditions for products in die form and QML-Q versions

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
27-Jul-2009	1	First issue.



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